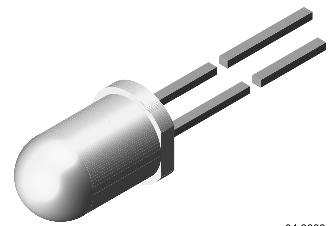
High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero

Description

TSHG6200 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted, plastic package.



94 8389

Features

- Peak wavelength: λ_p = 850 nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: φ = ± 10°
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth
- Good spectral matching to Si photodetectors
- Standard package: T-1¾ (∅ 5 mm)
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Pb-free

e2

Applications

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission

Parts Table

Part	Remarks
TSHG6200	MOQ: 4000 pcs

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	1	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient		R_{thJA}	270	K/W

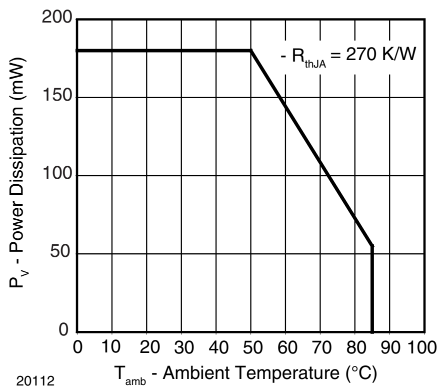


Figure 1. Power Dissipation Limit vs. Ambient Temperature

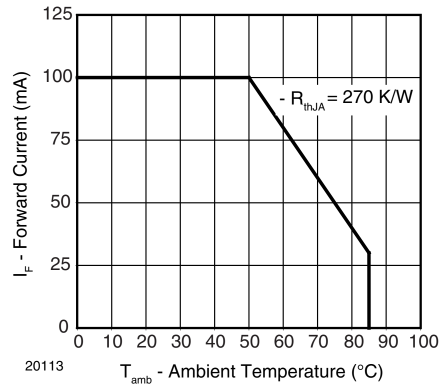


Figure 2. Forward Current Limit vs. Ambient Temperature

Basic Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.5	1.8	V
	I_F = 1 A, t_p = 100 µs	V_F		2.3		V
Temp. coefficient of V_F	I_F = 1 mA	TK_{VF}		- 1.8		mV/K
Reverse current	V_R = 5 V	I_R			10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		125		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	80	160	400	mW/sr
	I_F = 1 A, t_p = 100 µs	I_e		1600		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		50		mW
Temp. coefficient of ϕ_e	I_F = 100 mA	$TK\phi_e$		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I_F = 100 mA	λ_p		850		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		40		nm
Temp. coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.25		nm/K
Rise time	I_F = 100 mA	t_r		20		ns
Fall time	I_F = 100 mA	t_f		13		ns
Cut-off frequency	I_{DC} = 70 mA, I_{AC} = 30 mA pp	f_c		20		MHz
Virtual source diameter		∅		3.7		mm

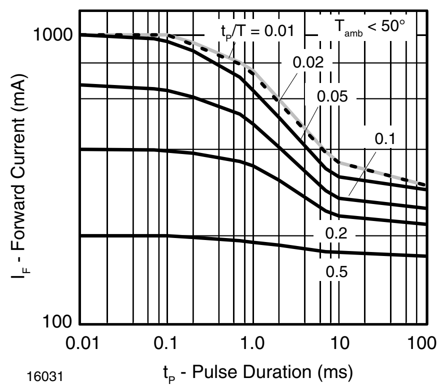


Figure 3. Pulse Forward Current vs. Pulse Duration

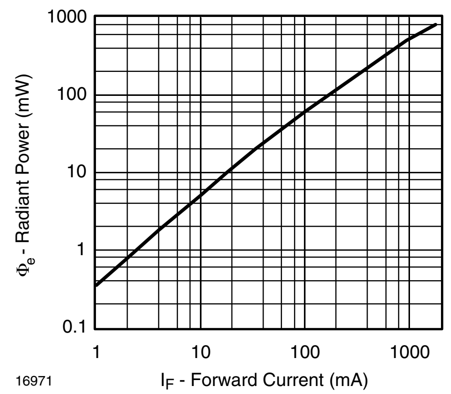


Figure 6. Radiant Power vs. Forward Current

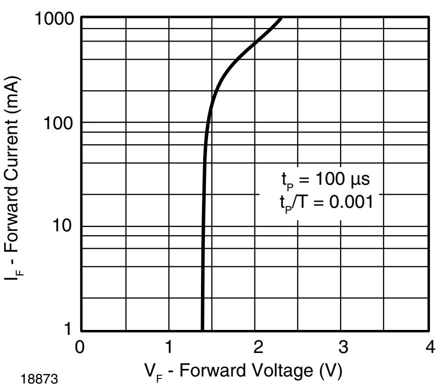


Figure 4. Forward Current vs. Forward Voltage

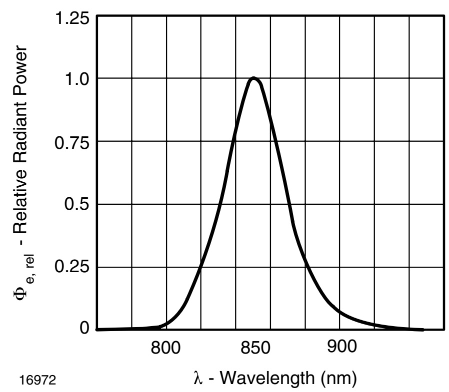


Figure 7. Relative Radiant Power vs. Wavelength

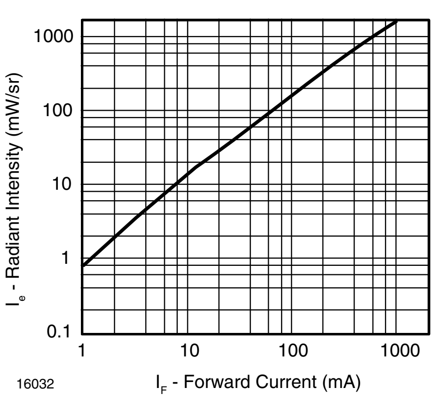


Figure 5. Radiant Intensity vs. Forward Current

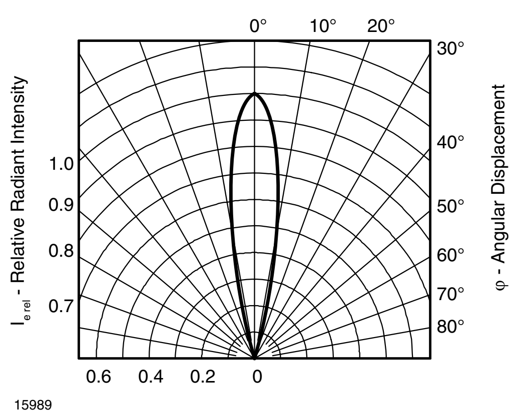
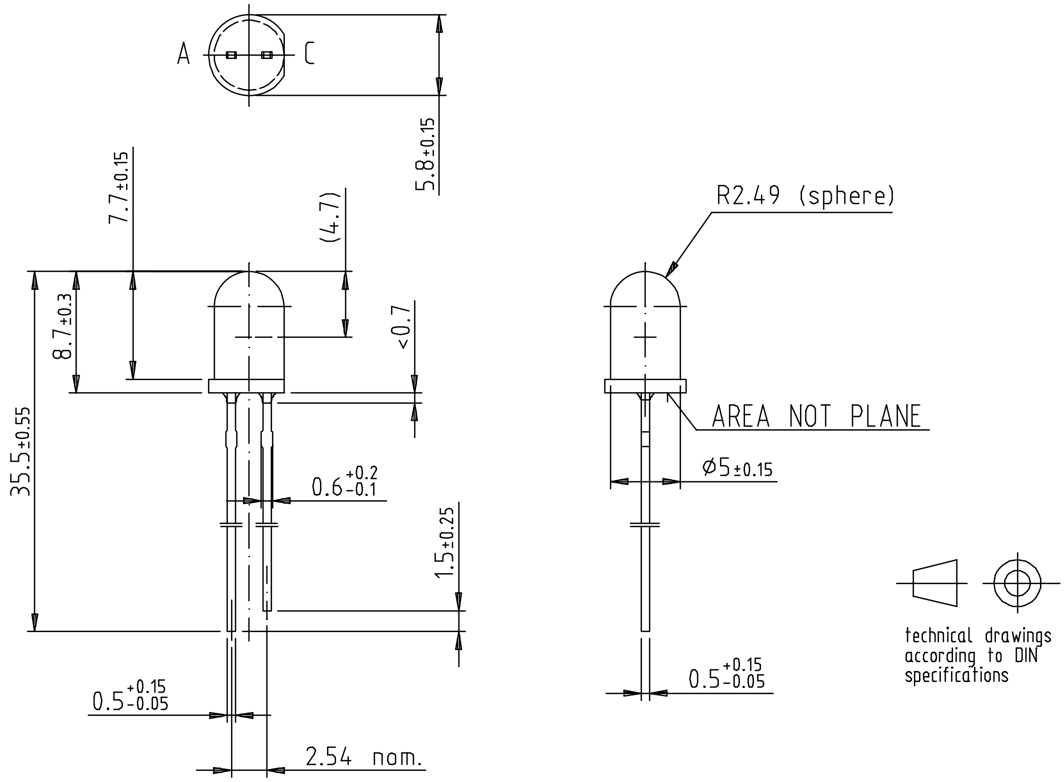


Figure 8. Relative Radiant Intensity vs. Angular Displacement

Package Dimensions in millimeters



95 10917

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.
Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.